TOSHIBA Bipolar Integrated Circuit Silicon Monolithic

TA2123AFG

1.5V Stereo Headphone Amplifier

The TA2123AFG is the system amplifier IC which is developed for playback stereo headphone equipments. It is built in dual auto—reverse preamplifiers, dual power amplifiers with bass / treble boost function, AMS (automatic music sensor) function, beep function, AGC for power amplifier etc.



Weight: 0.17g (typ.)

Features

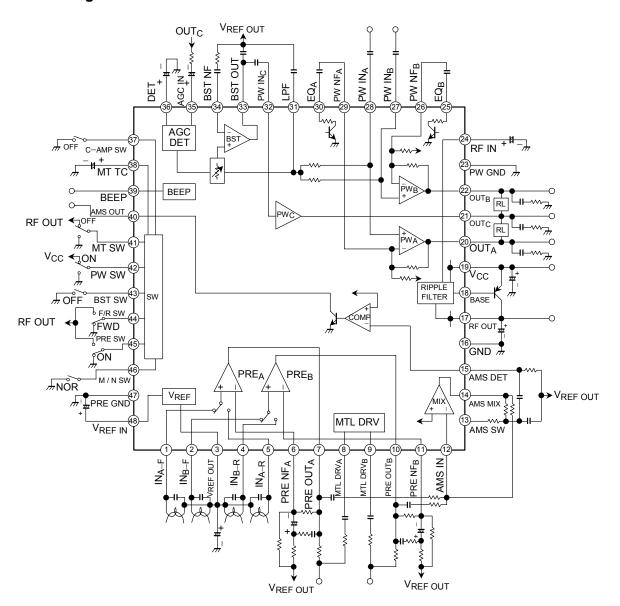
- Power amplifier stage
 - In case of output coupling type, the supply current decreases.
 (built-in center amplifier switch)
 - Built-in bass boost function
 - Built-in treble boost function
 - Built-in power amplifier muting function
 - Built-in input terminal for beep signal
 - Built-in input capacitor for reducing buzz noise
 - GV = 24dB (typ.)
 - Built-in AGC circuit (in case of boost mode, this circuit operates.)
- Low supply current

 $(V_{CC} = 1.3V, f = 1kHz, R_L = 32\Omega, T_a = 25$ °C, typ.)

	No Signal	0.1mW × 2	0.5mW × 2	
Output coupling type	1.5mA	3.0mA	5.0mA	
OCL type	2.2mA	4.9mA	8.6mA	

- · Preamplifier stage
 - Auto-reverse compatible
 - · Built-in input capacitor for reducing buzz noise
 - Input coupling condensor-less
 - Built-in metal mode drivers
 - Preamplifier muting function
- Built-in ripple filter circuit
- Built-in AMS (automatic music sensor) function (mixer amplifier and level comparator)
- Built-in power switch
- Operating supply voltage range (Ta = 25°C)
 VCC (opr) = 0.95~2.2V

Block Diagram



Terminal Explanation (terminal voltage: Typical terminal voltage at no signal with test circuit, V_{CC} = 1.3V, Ta = 25°C)

	Terminal	Function	Internal Circuit	Terminal Voltage
No.	Name			(V)
1	IN _{A-F}	Input of preamplifier	♥ VREF OUT	
2	IN _{B-F}	F / R SW (pin 44) - "L" level: Pin 1 / 2	FWD REV	0.73
4	IN _{B-R}	"H" level: Pin 4 / 5	<u></u>	00
5	IN _{A-R}	Refer to application note 3 (2)	J10pF 5pF 10pF	
6	PRE NF _A	NF of preamplifier FWD REV		0.7
11	PRE NF _B	THE OF PROGRESSION	₩ #	5
3	V _{REF} OUT	Output of reference circuit		0.73
48	V _{REF IN}	Input of reference circuit		0.73
7	PRE OUT _A	Output of preamplifier	<u>*</u>	0.44
10	PRE OUT _B	Catput of proamplino	*	
8	MTL DRV _A	Metal driver terminal		
9	MTL DRV _B	On resistance: 90Ω (typ.)	7 7	
12	AMS IN	Input of mixer amplifier for AMS signal		0.7
14	AMS MIX	Output of mixer amplifier for AMS signal	V _{REF} OUT	0.7
13	AMS SW	AMS sensitivity changeover switch (this switch synchronizes with the MT SW)	MT SW ON : CURRENT SOURCE→ON MT SW OFF : CURRENT SOURCE→OFF	_

	Terminal	Function	Internal Circuit	Terminal Voltage
No.	Name	T diretion	internal circuit	(V)
15	AMS DET	Input of AMS comparator circuit		0.73
40	AMS OUT	Output of AMS comparator circuit High level: Rectangular pulse Low level: "H"	V _{REF} OUT "" """	_
16	GND	_	_	0
17	RF OUT	Output of ripple filter Ripple filter circuit supplies internal circuit except power drive stage with power source	VCCO RF OUT	1.22
18	BASE	Base biasing terminal of transistor for ripple filter	48.5 K	0.5
19	V _{CC}	_		1.3
24	RF IN	Ripple filter terminal		1.23
20	OUTA	Output of power amplifier	to ADD amplifier	0.56
22	OUTB	Output of power amplifier 20kΩ VREF OUT		0.00
26	PW NF _B	NF of power amplifier		0.73
29	PW NF _A	The or power amplitude	7001.0	0.70
27	PW INB	Input of power amplifier (this terminal also has function of	29 2κΩ V _{REF OUT}	0.73
28	PW INA	an ADD amplifier input.)		0.73
21	OUT _C	Output of center amplifier	20kΩ VREF OUT	0.56
32	PW INC	Input of center amplifier	$ \begin{array}{c} 30k\Omega \\ 2k\Omega \\ \end{array} $ VREF OUT	0.73
23	PW GND	Power GND for power drive stage	_	0
25	EQB	Equalizer circuit (this circuit synchronizes with the BST SW)	1.8kΩ / G 39	_
30	EQA	• Input impedance : 1.9Ω (typ.)		

	Terminal	Function	Internal Circuit	Terminal Voltage
No. 31	Name	Low pass filter terminal of bass boost	20kΩ PW IN 10kΩ 10kΩ VREF OUT	(V) 0.73
33	BST OUT	Output of boost amplifier	VREF OUT. C1 E20kΩ 33	0.73
34	BST NF	NF of boost amplifier	100kΩ 	0.73
35	AGC IN	Input of boost AGC circuit The input level to the boost amplifier is controlled by the input level of this terminal. Input impedance: 10kΩ (typ.)	OUTC→ W_H + G5	0.73
36	DET	Smoothing terminal of boost AGC circuit	+ 38	_
37	C-AMP SW	Center amplifier on / off switch Output type of power amplifier OCL type: OPEN (C-AMP ON) Output coupling type: GND (C-AMP OFF)	Center amplifier	_
38	MT TC	Smoothing terminal of MT SW In order to reduce a pop noise at power amplifier on / off switching	# 4 10 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	0.7

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	Terminal	From editions	late and Oisse it	Terminal
No.	Name	- Function	Internal Circuit	Voltage (V)
39	BEEP	Input of beep signal This terminal receives beep signal of a microcomputer etc. This terminal should be set as high impedance or "H" when not using this function	Power amplifier	0.7
41	MT SW	Muting switch of power amplifier Power amp. on: "H" level Power amp. off: "L" level Refer to application note 3 (2)		ı
44	F/RSW	Forward / reverse switch Forward: "L" level Reverse: "H" level Refer to application note 3 (2)	47kΩ γ 47kΩ	ı
45	PRE SW	Muting switch of preamplifier Preamp. on: "L" level Preamp. off: "H" level Refer to application note 3 (2)	לת לת	_
42	PW SW	Power on / off switch IC on: "H" level IC off: "L" level Refer to application note 3 (2)		П
43	BST SW	Boost on / off switch BST on: OPEN / "H" level BST off: "L" level Refer to application note 3 (2)	20kΩ ,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	-
46	M/NSW	Metal / normal mode switch Metal mode: OPEN / "H" level Normal mode: "L" level Refer to application note 3 (2)	10kΩ	_
47	PRE GND	Power GND for power drive stage	_	0

Application Note

- 1. Preamplifier stage
 - (1) Output DC voltage of preamplifier

Output DC voltage of preamplifier is determined by external resistors R1 and R2 as shown in Fig.1.

 $V_{O (PRE)} = V_{REF OUT} - \Delta V \times (R2 / R1 + 1)$

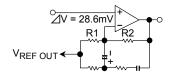


Fig.1 Output DC voltage of preamplifier

- $V_{REF\ OUT} = 0.73V\ (typ.)$
- ΔV is an offset voltage which is designed to 28.6mV.

It is as follows in case that the DC voltage is calculated by the constant of a test circuit.

Vo (PRE) =
$$0.73$$
V -28.6 mV (200 k Ω / 22 k Ω + 1) = 0.44 V

Output DC voltage of preamplifier should be fixed about $V_{\rm CC}$ / 2, because preamplifier get a enough dynamic range.

(2) AMS (automatic music sensor) function

A block diagram is shown in Fig.2. This function can AMS (automatic music sensor) and BS (blank skip).

- The comparator input level is higher than comparator sensitivity.
 - →Rectangle wave is outputted.
- The comparator input level is lower than comparator sensitivity.
 - →High level is outputted.

The sensitivity changeover is determined by AMS switch (the comparator sensitivity doesn't change.).

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Automatic music sensor mode

The AMS SW is also turned on when the MT SW is turned on. And the comparator input level is determined by external resistors (R4~R6) and capacitors (C3, C4) from mixer amplifier output level.

The transfer function is as follows.

$$\begin{split} V_O \, / \, V_i = & \, R3 \, / \, [R1 \cdot R2 \, / \, (R1 + R2)] \, \times \{ j_\omega C4 \cdot R5 \cdot R6 \, / \, [R4 \cdot R5 + j_\omega \, (C3 \cdot R4 \cdot R5 + C4 \cdot R4 \cdot R5 + C4 \cdot R4 \cdot R5 + C4 \cdot R5 \cdot R6) - \omega^2 C3 \cdot C4 \cdot R4 \cdot R5 \cdot R6] \} \end{split}$$

Blank skip mode

The AMS SW is also turned of when the MT SW is turned off. And the comparator input level is determined by external resistors (R4, R6) and capacitors (C3, C4) from mixer amplifier output level.

The transfer function is as follows.

 $V_O \ / \ V_i = R3 \ / \ [R1 \cdot R2 \ / \ (R1 + R2)] \times \\ \{j_\omega C4 \cdot R6 \ / \ [1 + j_\omega \ (C3 \cdot R4 + C4 \cdot R4 + C4 \cdot R6) - \omega^2 C3 \cdot C4 \cdot R4 \cdot R6]\}$

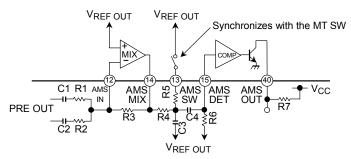


Fig.2 AMS system

2. Power amplifier stage

(1) Input of power amplifier

Each input signal should be applied through a capacitor. In case that DC current or DC voltage is applied to each amplifier, the internal circuit has unbalance and the each amplifier doesn't operate normally. It is advised that input signal refer to VREF voltage, in order to reduce a pop noise or low frequency leak.

(2) Output application

This IC can chose the output coupling type and OCL type. The C–AMP SW should be connected to GND in case that the output coupling type is chosen. The supply current decreases when not using the bass boost function.

- (3) Bass boost function
 - (a) System

This IC has the bass boost function in power amplifier stage. After this system adds the low frequency ingredient of side amplifier, it is applied into the center amplifier. And the bass boost level is controlled by the variable impedance circuit (Fig.3)

- Flow of the bass boost signal
 Variable impedance circuit→Boost amplifier→Center amplifier
- Flow of the bass boost level Output of center amplifier—AGC DET (level detection) \rightarrow Variable impedance circuit operation

The system of treble boost function is realized by frequency characteristic adjustment of the side amplifier.

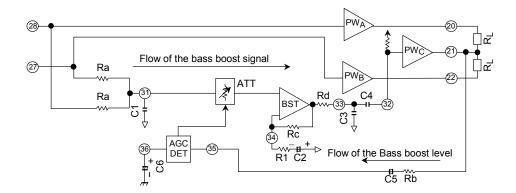


Fig.3 Bass boost system

(b) AGC circuit

The AGC circuit of bass boost function is realized by the variable impedance circuit. The AGC DET circuit detects the low frequency level of center amplifier. When this level becomes high, the variable impedance circuit operates, and this circuit attenuates the input level of center amplifier.

The AGC DET circuit is the current input, so that the output voltage of ADD amplifier is changed into the current ingredient by resistor Rb and capacitor C5 which are shown in Fig.3. And it is smoothed and detected by DET circuit (pin 36). And the direct current should not be applied to the AGC IN circuit, because, as for the circuit, the sensitivity setup is high.

Moreover, the AGC signal level is decreased in case that the resistor R5 is connected with the capacitor C5 in series. And the AGC point can be changed. But the center amplifier is clipped in the low frequency in case that the resistor R5 is larger.

(c) Bass boost

The signal flow of bass boost function is as follows, refer to Fig.4.

LPF (internal resistors 2R1 and external capacitor C1)

- →ATT (variable impedance circuit)
- →HPF (BST amplifier)
- →BPF (LPF: internal resistor R4 and external capacitor C3, HPF: external capacitor C4 and internal resistor R5)
- →Center amplifier

The center amplifier signal becomes the reverse phase, because the phase of audio frequency range is reversed with two LPFs.

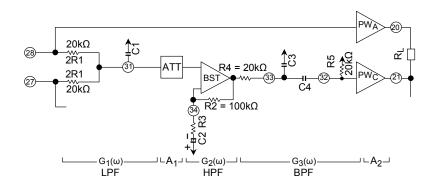


Fig.4 Block diagram of bass boost

The transfer function of bass boost is as follows from Fig.4.

$$G(\omega) = G_1(\omega) \cdot A_1 \cdot G_2(\omega) \cdot G_3(\omega) \cdot A_2$$

The bass boost effect is changed by external resistor or external capacitor. The transfer function and cut off frequency are as follows.

(1) Transfer function of LPF

$$G_1(\omega) = 1 / (1 + j\omega C1 \cdot R1)$$

$$\mathrm{fL} = 1 \: / \: 2 \: \pi \: \mathrm{C1} \boldsymbol{\cdot} \mathrm{R1}$$

(2) Transfer function of BPF

$$G_3(\omega) = j\omega C4 \cdot R5 / [1 + j\omega (R4 \cdot C3 + R5 \cdot C3 + C4 \cdot R4) - \omega^2 R4 \cdot C3 \cdot R5 \cdot C4]$$

$$f_O = 1/2\pi \sqrt{R4 \cdot C3 \cdot R5 \cdot C4}$$

(3) HPF gain and cut off frequency

$$G_2(\omega) = 1 + R_2 / (R_3 + 1 / j\omega C_2)$$

$$f_{HC} = 1 / (2 \pi R3 \cdot C2)$$

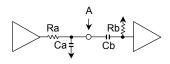
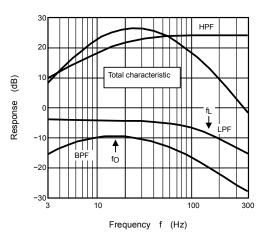


Fig.5 BPF



Graph.1 Characteristic of bass boost

(4) fo and fL

The f_L and f_O should be set up out of the audio frequency range. In case that the f_O and f_L is inside of audio frequency range and AGC circuit operates, the voltage gain decrease.

(5) HPF

The fHC should be made 1/2 or less frequency as compared with the fL or fO. The phase difference is large near the fHC, so that the bass boost level runs short. And the HPF gain of middle or high frequency range should be set to 10dB or more.

(4) Treble boost

The EQ terminal is synchronizes with the BST SW, and the input impedance is changed.

BST OFF: $100k\Omega$ (typ.) BST ON: $1.9k\Omega$ (typ.)

The voltage gain increase $6 \, dB$ (typ.) at high frequency range in case that the capacitor CX is connected between the EQ terminal and the PW NF terminal.

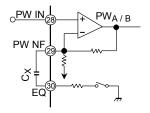


Fig.6 Treble boost

(5) Cross talk of output coupling type

In case of output coupling mode, the cross talk is determined by resistor R_L and capacitor C which are connected with power amplifier output as shown in Fig.7.

The formula is shown below.

$$\begin{array}{l} G\;(\omega) = 1\:/\:2\:\left[\:1 + j\omega C\;(R_L\:/\:2)\right] \\ CT = 20 log\:|\:G_V\:|\: = 20 log\;\left[\:1\:/\:2\:\left[\:\sqrt{1 + (\omega\:/\:\omega_0)^2}\:\right]\right],\;\omega_0 = 1\:/\:C\;(R_L\:/\:2) \\ At\;f = 1kHz,\;C1 = 220 \mu F,\;R_L = 32 \Omega,\;The\;cross\;talk\;becomes\;about\;33\;dB. \end{array}$$

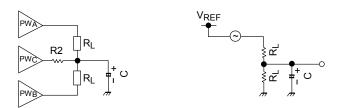


Fig.7 Cross talk of output coupling type

3. Total

(1) Ripple filter

It is necessary to connect a low saturation transistor (2SA1362 etc.) for ripple filter, because this IC doesn't have transistor for ripple filter. Care should be taken to stabilize the ripple filter circuit, because the ripple filter circuit supplies internal circuit except power drive stage with power source.

(2) Switch terminal

(a) PW SW

It is necessary to connect an external pull–down resistor with terminal PW SW, in case that this IC is turned on due to external noise etc. (The PW SW sensitivity is designed highly.)

(b) MT SW, BST SW, F/R SW, PRE SW, M/N SW

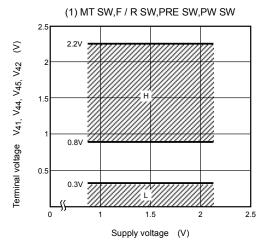
The current flows through terminals of MT SW, BST SW, PRE SW and M / N SW, in case that these terminals are connected with $V_{\rm CC}$ line independently, even though the PW SW is off-mode. It is necessary to connect an external pull-down resistor with each terminals in case that IC is turned on due to external noise etc. These switches are designed highly.)

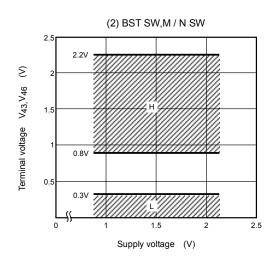
 The pop noise at turning on / off MT SW can be reduced by the external capacitor of the MT TC terminal.

(c) C-AMP SW

The C–AMP SW terminal should not be connected with high voltage of $V_{\rm CC}$ etc., because internal circuit is broken.

(d) Sensitivity voltage of each switch (Ta = 25°C)





		MT SW (V ₄₁)	F / R SW (V ₄₄)	PRE SW (V ₄₅)	PW SW (V ₄₂)
	'H'	Muting OFF	REV mode	Preamp. OFF	IC ON
I	'L'	Muting ON	FWD mode	Preamp. ON	IC OFF

	BST SW (V ₄₃)	M / N SW (V ₄₆)
'H', open	BST ON	Metal mode
Ļ	BST OFF	Normal mode



(3) Capacitor

Small temperature coefficient and excellent frequency characteristic is needed by capacitor below.

- Oscillation preventing capacitors for power amplifier output
- Capacitor between VREF and GND
- Capacitor between VCC and GND
- Capacitor between RF OUT and GND

Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Supply voltage	V _{CC}	4.5	V
Output current (PW AMP.)	I _{O (peak)}	100	mA
Power dissipation	P _D (Note)	750	mW
Operating temperature	T _{opr}	<i>–</i> 25∼75	°C
Storage temperature	T _{stg}	-55~150	°C

Note: Derated above Ta = 25°C in proportion of 6mW / °C

Electrical Characteristics

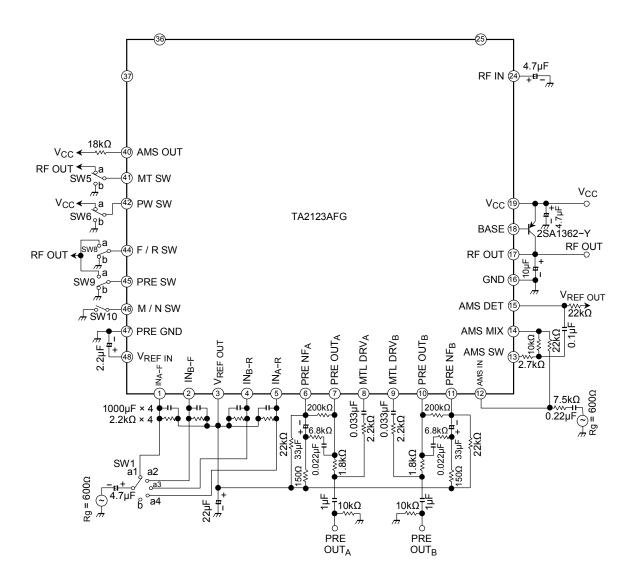
Unless Otherwise Specified: V_{CC} = 1.3V, Ta = 25°C, f = 1kHz, SW1: b, SW2: b, SW3: a, SW4: OPEN SW5: a, SW6: a, SW7: ON, SW8: a / b, SW9: b,

Preamplifier: Normal Mode, R_g = 2.2k Ω , R_L = 10k Ω , SW1: a Power Amplifier: R_g 600 Ω , R_L = 32 Ω , SW2: a

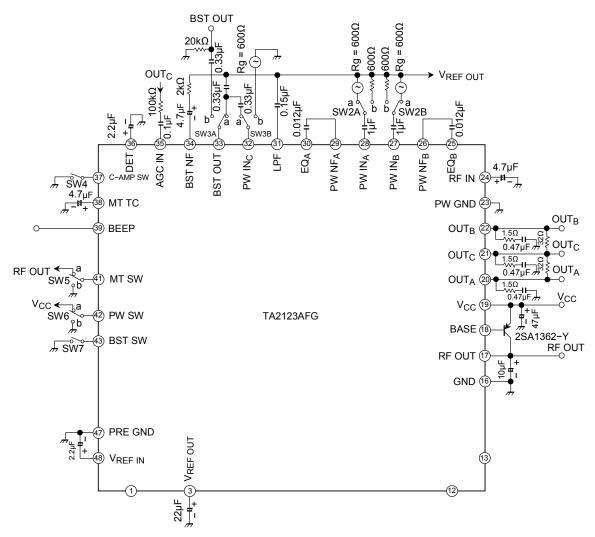
	Characteristics	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Qui	escent supply current 1	I _{CCQ1}	_	OCL mode, PRE + PW	_	2.2	4.0	
Qui	escent supply current 2	I _{CCQ2}	_	OCL mode, PRE: OFF SW9: a	_	1.7	3.0	
Qui	escent supply current 3	I _{CCQ3}	_	Coupling mode PRE + PW, SW4: ON	_	1.5	2.7	mA
Qui	escent supply current 4	I _{CCQ4}	_	Coupling mode PRE: OFF, SW4: ON SW9: a	_	1.0	1.8	
	Open loop voltage gain	G _{VO}	_	$V_0 = -22 dBV$ NF resistor (150 Ω): Short	65	80	_	dB
	Closed loop voltage gain	G _{VC}	_	$V_0 = -22 dBV$	_	35	_	
	Maximum output voltage	V _{om1}	_	THD = 1%	160	250	_	mV_{rms}
	Total harmonic distortion	THD1	_	V_{CC} = 1V, V_0 = -22dBV	_	0.08	0.3	%
o. stage	Equivalent input noise voltage	V _{ni}	_	Rg = $2.2k\Omega$ BPF: $20Hz\sim20kHz$ NAB (G_V = $35dB$, f = $1kHz$) SW1: b	_	1.7	2.7	μV _{rms}
Preamp.	Cross talk (CH-A / CH-B)	CT1	_	$V_0 = -22 dBV$	_	60	_	
Б	Cross talk (forward / reverse)	CT2	_		_	62	_	dB
	Ripple rejection ratio	RR1	_	$f_r = 100Hz, V_r = -32dBV$ BPF = 100Hz	_	54	_	
	Preamplifier muting attenuation	ATT1	_	V _o = −22dBV SW9: b→a	_	84	_	
	Driver on resistance	R1	_	I _L = 100μA, SW10: OPEN	_	90	_	Ω
AM:	S sensitivity 1	AMS1	_	SW5: b	-58.3	-56.3	-54.3	dBV
AM:	S sensitivity 2	AMS2	_	SW5: a	-69.7	-67.7	-65.7	ubv
For	ward mode on voltage	V ₄₄	_		0	_	0.3	V
Rev	verse mode on current	144	<u> </u>		5	_	_	μΑ
Pre	amplifier on voltage	V ₄₅	_	,	0	_	0.3	V
Pre	amplifier off current	I ₄₅		V _{CC} = 0.95V	5	_	_	μA
Met	al mode on voltage	V _{46 (M)}			0.8	_	0.95	V
Nor	mal mode on voltage	V _{46 (N)}	_		0	_	0.3	V

_		1	1						
	Characteristics	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit	
	Voltage gain 1	G _{V1}	_	$V_0 = -22 dBV$	_	24	_	dB	
	Channel balance	СВ	_	V ₀ 2200 V	-1.5	0	+1.5		
	Voltage gain 2	G _{V2}	_	$V_{in (A)} = V_{in (B)} = -V_{in (C)}$ $V_{o} = -22dBV$	28	30	32		
	Output power	Po	_	V _{CC} = 1.5V THD (A) = THD (B) = 10%	3	6	_	mW	
o. stage	Total harmonic distortion	THD	_	P _o = 1mW	_	0.1	0.8	%	
Power amp.	Output noise voltage	V _{no}	_	Rg = 600Ω, SW2: b BPF = 20Hz~20kHz	_	40	80	μV _{rms}	
Pov	Cross talk	CT3	_	$V_0 = -22 dBV$	34	43	_		
	Ripple rejection ratio	RR2	_	$V_{CC} = 1V, f_r = 100Hz$ $V_r = -32dBV, BPF = 100Hz$	_	70	_	dB	
	Power amplifier muting attenuation	ATT2	_	V _o = −22dBV SW5: a→b	_	72	_		
	Beep signal input sensitivity	SEN	_	V ₀ = -62dBV, SW5: OPEN	0.7	1.3	2.2	μA _{p-p}	
	Voltage gain 3	G _{V3}	_	f = 40Hz, V _{in} = -64dBV SW7: Open Monitor: C-AMPGND	41	44	47	- dB	
ηρ. stage	Voltage gain 4	G _{V4}	_	f = 40Hz, V _{in} = -47dBV SW7: Open Monitor: C-AMPGND	27.5	30.5	33.5	QB	
Boost amp.	Maximum output voltage	V _{om2}	_	f = 40Hz, THD = 1% SW3: b, SW7: Open	_	86	_	mV _{rms}	
B	Muting attenuation	ATT3	_	f = 40Hz, V ₀ = −32dBV SW7: Open→on	_	53	_	dB	
	Equalizer on resistance	R2	_	I _L = 100μA, SW7: Open	_	1.9	_	kΩ	
Rip	ole filter output voltage	V _{RF OUT}	_	V _{CC} = 1V, I _{RF} = 20mA	0.89	0.92	_	V	
Rip _l ratio	ole filter ripple rejection	RR3	_	V_{CC} = 1V, I_{RF} = 20mA BPF = 100Hz, f_r = 100Hz V_r = -32dBV	35	42	_	dB	
Pov	ver amplifier on current	I ₄₁	_		5	_	_	μA	
Pov	ver amplifier off voltage	V ₄₁	_		0	_	0.3	V	
Pov	ver on curent	l ₄₂	_	V = 0.05V	5	_	_	μA	
Pov	ver off voltage	V ₄₂	_	V _{CC} = 0.95V	0	_	0.3	V	
Boo	st on voltage	V _{43 (ON)}	_		0.8	_	0.95	V	
Boo	st off voltage	V _{43 (OFF)}	_		0	_	0.3	V	

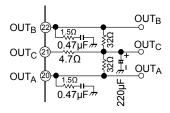
Test Circuit (preamplifier stage)



Test Circuit (power amplifier stage)



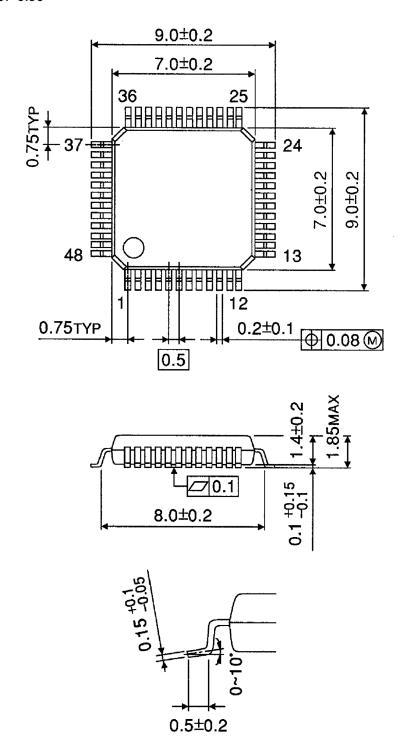
Output circut of output coupling type



Package Dimensions

LQFP48-P-0707-0.50

Unit: mm



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Weight: 0.17g (typ.)

About solderability, following conditions were confirmed

- Solderability
 - (1) Use of Sn-63Pb solder Bath
 - solder bath temperature = 230°C
 - · dipping time = 5 seconds
 - · the number of times = once
 - · use of R-type flux
 - (2) Use of Sn-3.0Ag-0.5Cu solder Bath
 - · solder bath temperature = 245°C
 - dipping time = 5 seconds
 - · the number of times = once
 - · use of R-type flux

RESTRICTIONS ON PRODUCT USE

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